

N-channel MOSFET

FEATURES

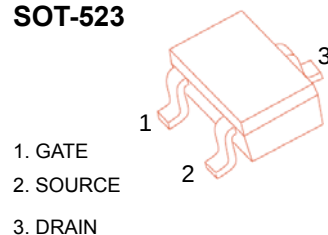
- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for portable equipment
- Easily designed drive circuits
- Easy to parallel

Marking: KN

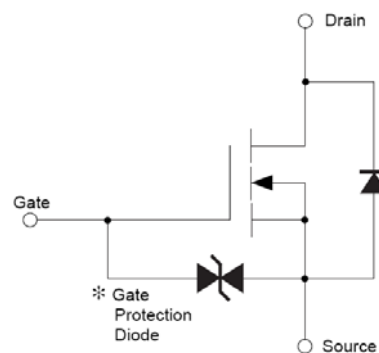
MOSFET MAXIMUM RATINGS (Ta = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current	0.1	A
R _{θJA}	Thermal Resistance, Junction-to-Ambient	833	°C /W
P _D	Power Dissipation	0.15	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

SOT-523



Equivalent circuit

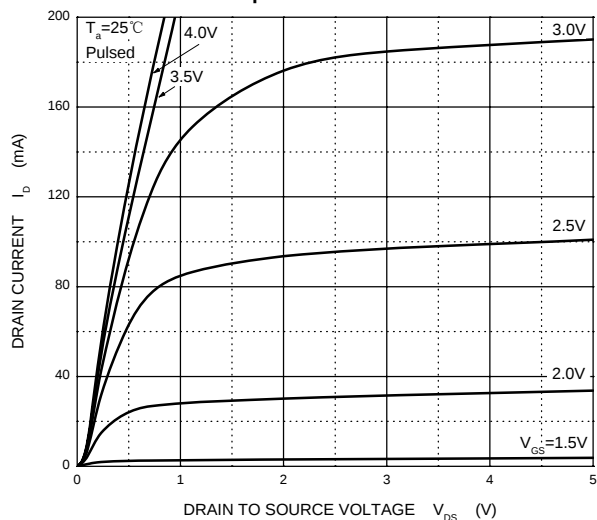


MOSFET ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

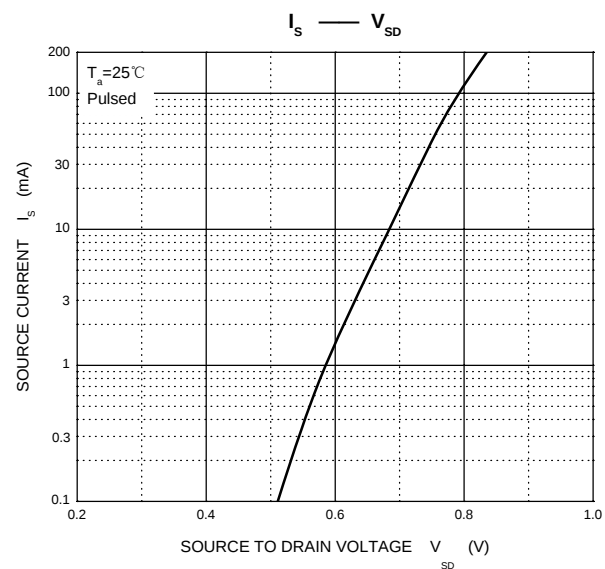
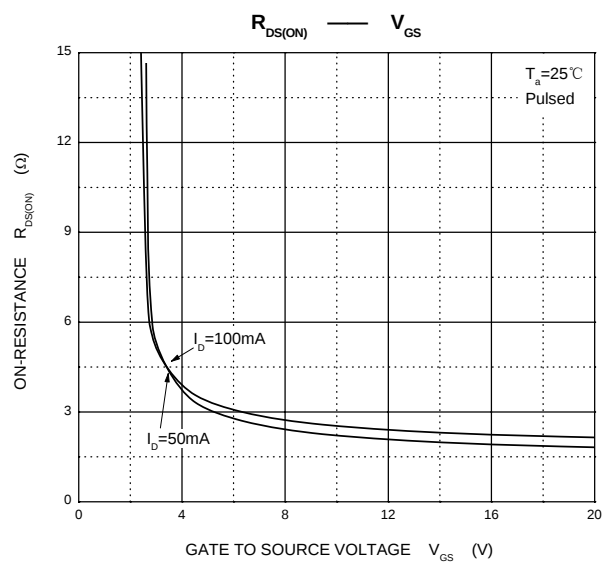
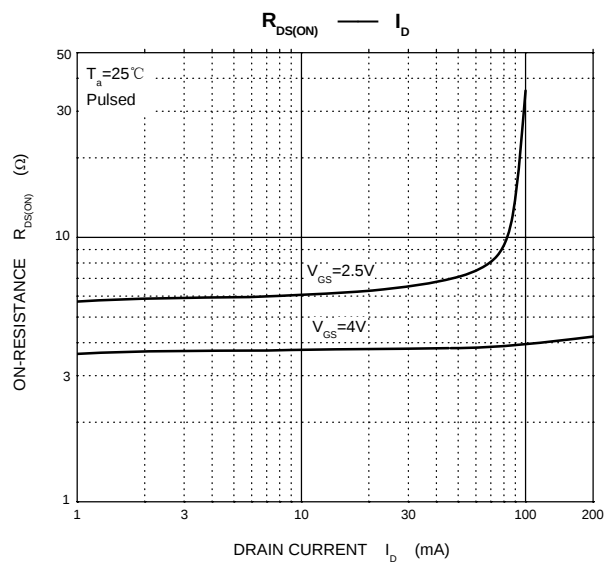
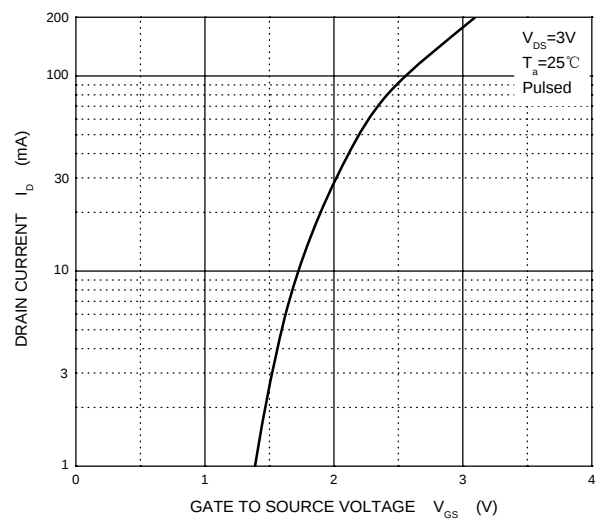
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0V, I _D = 10μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} = 0V			1	μA
Gate –Source leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V			±10	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = 3V, I _D =100μA	0.8		1.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 4V, I _D =10mA			8	Ω
		V _{GS} =2.5V, I _D =1mA			13	Ω
Forward Transconductance	g _{FS}	V _{DS} =3V, I _D = 10mA	20			mS
Dynamic Characteristics*						
Input Capacitance	C _{iss}	V _{DS} =5V, V _{GS} =0V, f =1MHz		13		pF
Output Capacitance	C _{oss}			9		pF
Reverse Transfer Capacitance	C _{rss}			4		pF
Switching Characteristics*						
Turn-On Delay Time	t _{d(on)}	V _{GS} =5V, V _{DD} =5V, I _D =10mA, R _g =10Ω, R _L =500Ω,		15		ns
Rise Time	t _r			35		ns
Turn-Off Delay Time	t _{d(off)}			80		ns
Fall Time	t _f			80		ns

* These parameters have no way to verify.

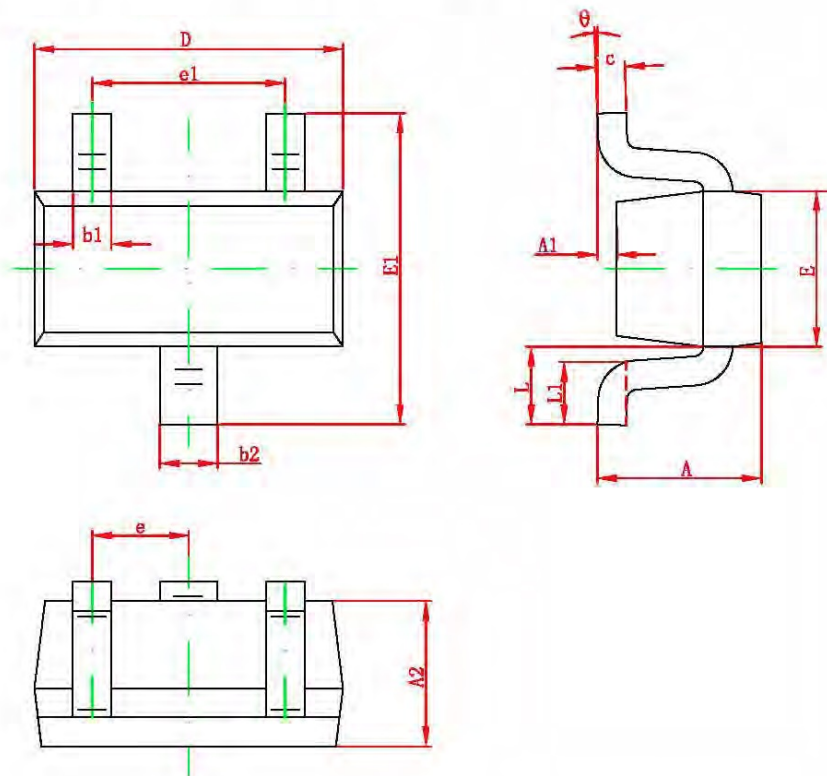
Output Characteristics



Transfer Characteristics



SOT-523 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°